TOSHIBA

CRG01,CRG02

Unit in mm

TOSHIBA RECTIFIER SILICON DIFFUSED TYPE

CRG01, CRG02

GENERAL PURPOSE RECTIFIER APPLICATIONS

Average Forward Current : $I_{F(AV)} = 0.7A$

Repetitive Peak Reverse Voltage: VRRM=100, 400V

: "S-FLAT" (Toshiba designation) Small Package

MAXIMUM RATINGS

CHARACTERISTIC		RATING	UNIT	
CRG01	V 7	100	v	
CRG02	VRRM	400	V	
Average Forward Current		0.7	A	
Peak One Cycle Surge Forward		15 (50Hz)	A	
Current (Non-Repetitive)		16.5 (60Hz)		
	T_{j}	-40~150	°C	
Storage Temperature Range		-40~150	°C	
	CRG02	$egin{array}{c} {\sf VRRM} \\ {\sf I_{F(AV)}} \\ {\sf ard} \\ {\sf I_{FSM}} \\ \end{array}$	$ \begin{array}{c c} \text{CRG01} & \text{V}_{\text{RRM}} & 100 \\ \hline \text{CRG02} & \text{I}_{\text{F}}(\text{AV}) & 0.7 \\ \hline \text{ard} & \text{I}_{\text{FSM}} & \frac{15(50\text{Hz})}{16.5(60\text{Hz})} \\ \hline & \text{T}_{\text{j}} & -40 {\sim} 150 \\ \hline \end{array} $	

 3.5 ± 0.2 0.65 ± 0.2 0.9 + 0.10.16 1.6 +0.2 1. ANODE 2. CATHODE **JEDEC EIAJ TOSHIBA** 3-2A1A

Weight: 0.013g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	TYP.	MAX.	UNIT
	V _{FM (1)}	$I_{\text{FM}} = 0.1A$	0.88	_	
Peak Forward Voltage	V _{FM (2)}	$I_{FM} = 0.7A$		1.1] v
	V _{FM} (3)	I _{FM} =1.0A	1.10	_	
Repetitive Peak Reverse Current	$I_{ m RRM}$	V _{RRM} =Rated	_	10	μ A
Thermal Resistance	rth (j-a)	On ceramic substrate	_	65	°C/W
	(DC)	On glass-epoxy substrate	_	130	C/W
		A S 性 医 W	NW.D	75C-	COM

The information contained herein is subject to change without notice

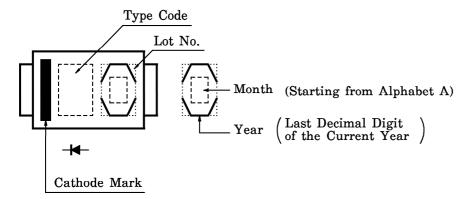
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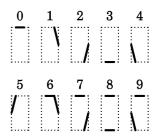
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MARKING



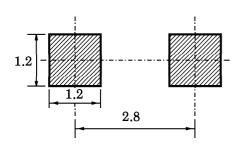
FOLLOWING INDICATES
THE DATE OF MANUFACTURE

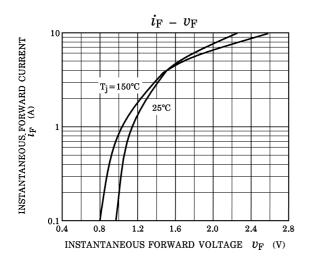


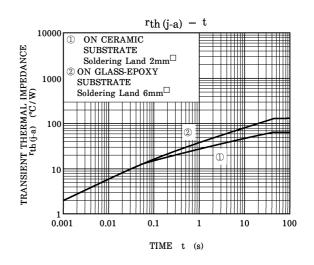
TYPE	CODE
CRG01	G1
CRG02	G2

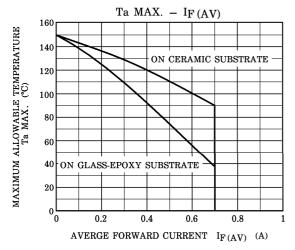
STANDARD SOLDERING PAD

Unit: mm









	ON CERAMIC SUBSTRATE	ON GLASS- EPOXY SUBSTRATE
Soldering Land	2mm [□]	6mm□
Substrate Size	50mm [□]	50mm [□]
Substrate Thickness	0.64t	1.6t

	30	SURGE FORWARD CURRENT (NON - REPETITIVE)					
CURRENT	25	Ta=25°C, f=50 Half Sine Wayeform)Hz				
			\mathbb{H}				
WARD (A)	20		\parallel				
PEAK SURGE FORWARD CURRENT IFSM (A)	15						
	10		\pm				
PEAK	5		\mathbb{H}				
	0	1 10	10				
		NUMBER OF CYCLES	10				